

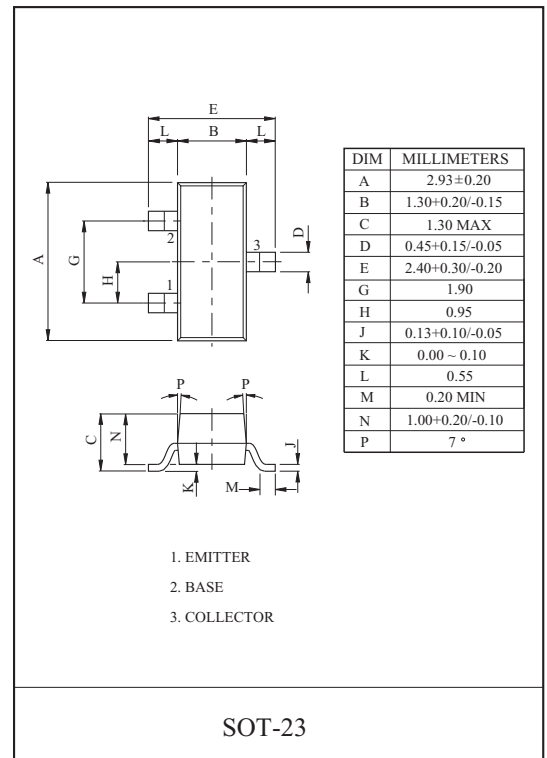
GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

FEATURE

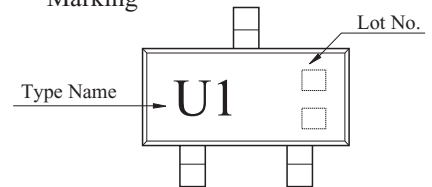
- Super Mini Packaged Transistors for Hybrid Circuits.

MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CEO}	50	V
Collector-Emitter Voltage	V_{CEO}	45	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	500	mA
Emitter Current	I_E	-500	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-65 ~ 150	°C



Marking



ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	45	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=10\mu A, V_{BE}=0$	50	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	5.0	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB}=20V, I_E=0$	-	-	100	nA
		$T_a=150\text{ °C}, V_{CB}=20V, I_E=0$	-	-	5.0	μA
DC Current Gain	h_{FE}	$V_{CE}=1V, I_C=100mA$	100	-	600	
		$V_{CE}=1V, I_C=300mA$	70	-	-	
		$V_{CE}=1V, I_C=500mA$	40	-	-	
Base-Emitter Voltage	$V_{BE(ON)}$	$V_{CE}=1V, I_C=500mA$	-	-	1.2	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$	-	-	0.62	V
Transition Frequency	f_T	$I_C=10mA, V_{CE}=5V, f=100MHz$	-	200	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, f=1MHz$	-	6.0	-	pF